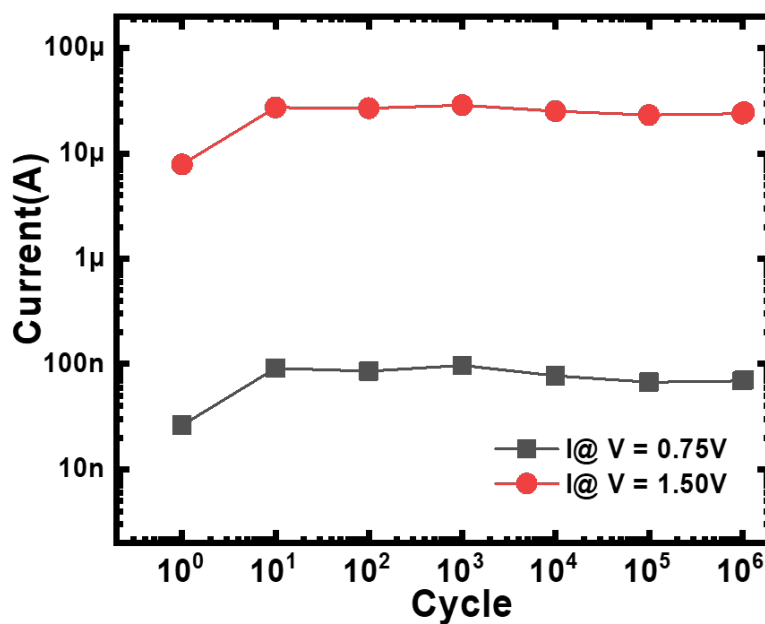


## Investigation of NbOx-based volatile switching device with self-rectifying characteristics

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### Appendix A Supplementary figure



**Figure A1** The endurance of the niobium-oxide based device is larger than 10<sup>6</sup>

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